

Type Designator: BLY11

Material of Transistor: Si

Polarity: NPN

Maximum Collector Power Dissipation (P_c): 10 W

Maximum Collector-Base Voltage $|V_{cb}|$: 20 V

Maximum Collector-Emitter Voltage $|V_{ce}|$: 20 V

Maximum Emitter-Base Voltage $|V_{eb}|$: 6 V

Maximum Collector Current $|I_c \text{ max}|$: 0.5 A

Max. Operating Junction Temperature (T_j): 200 °C

Transition Frequency (f_t): 100 MHz

Collector Capacitance (C_c): 47 pF

Forward Current Transfer Ratio (h_{FE}), MIN: 21

Noise Figure, dB: -

Package: TO3